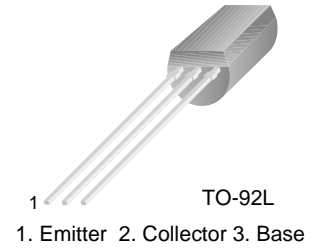


■ ■ APPLICATION: High Voltage Power Amplifier Applications.

■ ■ MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	200	V
Collector-emitter voltage	V_{CEO}	150	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^{\circ}\text{C}$


■ ■ ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	40		240		$V_{CE}=5\text{V}$, $I_C=10\text{mA}$
Collector Cut-off Current	I_{CBO}			0.1	μA	$V_{CB}=200\text{V}$, $I_E=0$
Emitter Cut-off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$, $I_C=0$
Collector-Base Breakdown Voltage	BV_{CBO}	200			V	$I_C=0.1\text{mA}$, $I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	150			V	$I_C=5\text{mA}$, $I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_E=0.1\text{mA}$, $I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	$I_C=10\text{mA}$, $I_B=1\text{mA}$
Gain bandwidth product	f_T		100		MHz	$I_C=10\text{mA}$, $V_{CE}=30\text{V}$
Common Base Output Capacitance	C_{ob}		3.5	5	PF	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$

■ ■ h_{FE} Classification

Classification	R	O	Y
h_{FE}	40~80	70~140	120~240